

Silicon Depletion-Mode TW Modulator



7 Capella Court Nepean, ON, Canada K2E 7X1

+1 (613) 224-4700 www.optiwave.com

Introduction (MZM)



- Mach Zehnder Modulator (MZM)
 - Phase shift is achieved from using Pockels Effect, Kerr, or carrier injection/depletion
 - Short and compact but requires higher voltage/power
 - Limited modulation speed (10-40 Gb/s)
- Building blocks
 - 1 Splitter
 - 1 Joiner
 - 2 Waveguides
- OptiSPICE Model
 - Explicit multilayer filter model is set up with a single layer
 - The change in the refractive index can be controlled by a voltage source
 - Can be configured as push-pull or asymmetric







Introduction (TW Modulator)



- Traveling Wave MZM
 - Modulation occurs the same way as MZM
 - Phase shift is achieved from using Pockels Effect, Kerr, or carrier injection/depletion
 - Longer device but uses lower voltage/power compared to regular MZM
 - Can achieve higher modulation speeds (~70 Gbit/s)
- Building blocks
 - 1 Splitter
 - 1 Joiner
 - 2 Transmission line electrodes
 - 2 Waveguides
- OptiSPICE Model
 - The waveguide consists of many layers with controllable refractive indexes
 - Each transmission line corresponds to a different metal contact connected to one of the waveguides
 - The waveguides and the transmission line models have the same length and the same number of sections
 - The refractive index of each layer is a function of the voltage in the corresponding section of the transmission line





Si-TWM Model Overview

- Modified transmission line model for PN Junction
- Sectionalized modulator arms (MLF + TL)
- $\Delta n \alpha E$ in each section (can be nonlinear)



*K. Zhu, V. Saxena and W. Kuang, "Compact Verilog-A modeling of silicon traveling-wave modulator for hybrid CMOS photonic circuit design," 2014 IEEE 57th International Midwest Symposium on Circuits and Systems (MWSCAS), College Station, TX, 2014, pp. 615-618.





Parameters

- Transmission line (model parameters)
 - 100 Sections (*Number of sections*)
 - Rtl = 2kohm/m
 - Ctl = 120 pf/m
 - Ltl = 500 nH/m
 - RS = 13e-3 ohm*m
 - CJ = 186 pf/m @(-3V Reverse Bias)
 - d = 2 mm (*Modulator length*)
- Transmission line (calculated parameters)
 - R0 = re(Z0) = 43 ohm @ 40 Ghz
 - neff = 3.4@ 40 Ghz
 - v = 8.8174e+07 m/s @ 40 Ghz
- Multilayer filter (model parameters)
 - n = 3.4 (Refractive index)
 - d = 2 mm (*Modulator length*)
 - 100 ML filter layers (*Number of sections*)
- Multilayer filter (calculated parameters)
 - v = c/n = 8.8174e+07 m/s
 - Vpi =1.3 V



TW Modulator - Si Parameters				
Name:	X2			
Model:	TW_MOD_Silicon_SUBCIRCUIT			
Mair	-			
_	1	-		
Disp	Name	Value	Units	Enabl
Disp	Name Modulator length	Value 2	Units mm	Enabl
Disp	Name Nodulator length Number of sections	Value 2 100	Units mm	Enabl





OptiSPICE TWM circuit



Transmission line characteristics



* Hao Xu, Xianyao Li, Xi Xiao, Zhiyong Li, Yude Yu and Jinzhong Yu, "Demonstration and Characterization of High-Speed Silicon Depletion-Mode Mach–Zehnder Modulators," in IEEE Journal of Selected Topics in Quantum Electronics, vol. 20, no. 4, pp. 23-32, July-Aug. 2014.





7

Eye diagram results for traveling wave modulator simulation (Ref design: TWMZM_Silicon.osch)







8

Velocity mismatch simulation

- In this simulation the refractive index of the waveguide was increased to reduce the velocity of the electric field
- As the velocity mismatch becomes more severe the change in the refractive index and the electric field traveling in the waveguide do not overlap long enough
- The reduced overlapping time decreases the total amount of phase shift accumulated by the traveling electric field, therefore the extinction ratio gets smaller

OptiSPICE simulation showing velocity mismatch in the traveling wave modulator (Ref design: TWMZM_Silicon_VelocityMismatch.osch)







9